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ning of each regular issue of the PCT Gazette.

(54) Title: **METHOD FOR PRODUCING TETRAFLUOROSILANE**

(57) Abstract: The invention relates to a method for producing tetrafluorosilane by decomposing hexafluorosilicic acid with sulfuric acid, which comprises: step 1 of decomposing hexafluorosilicic acid in concentrated sulfuric acid in the first reactor to give SiF<sub>4</sub> and HF and taking out the SiF<sub>4</sub>; step 2 of transferring part of the concentrated sulfuric acid solution of step 1 containing HF into the second reactor to react the HF with silicon dioxide fed thereinto, thereby producing SiF<sub>4</sub> containing (SiF<sub>3</sub>)<sub>2</sub>O; and step 3 of bringing the reaction product of step 2 containing (SiF<sub>3</sub>)<sub>2</sub>O and SiF<sub>4</sub> to the first reactor to react (SiF<sub>3</sub>)<sub>2</sub>O contained in the reaction product with HF to convert it into SiF<sub>4</sub> and then taking out the SiF<sub>4</sub> along with SiF<sub>4</sub> formed in step 1. According to the invention, high-purity SiF<sub>4</sub> can be obtained with (SiF<sub>3</sub>)<sub>2</sub>O being reduced, free from HF generated as a problematic side product in conventional method.

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